



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-31 A

Features

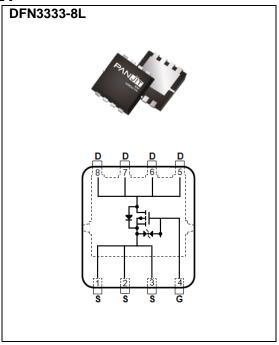
- RDS(ON), VGS@-10V, ID@-10A<19.1m Ω
- RDS(ON), VGS@-4.5V, ID@-6A<31.2m Ω
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETE	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	±25	V	
Continuous Drain Current(Note 3)	T _C =25°C		-31		
	T _C =100°C	I _D	-22	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-90		
Power Dissipation	T _C =25°C	D-	30	10/	
	T _C =100°C	Po	15	W	
Continuous Drain Current(Note 4)	T _A =25°C		-9	^	
	T _A =70°C	l _D	-7.6	Α	
Power Dissipation	T _A =25°C	D-	2.5	W	
	T _A =70°C	PD	1.8		
Single Pulse Avalanche Energy ^(Note 5)		Eas	36	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	$R_{ heta JC}$	5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60		





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static			_				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.8	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-10A	-	15.3	19.1	mΩ	
		V _{GS} =-4.5V, I _D =-6A	-	24	31.2		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA	
Coto Source Looke to Current		V _{GS} =±25V, V _{DS} =0V	-	-	±10		
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1	uA	
Dynamic ^(Note 6)							
Total Gate Charge	Qg	V 04V I 40A	-	22	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =-24V, I _D =-10A, V _{GS} =-10V	-	3	-		
Gate-Drain Charge	Q_{gd}	VGS=-10V	-	7	-		
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V, f=1MHz	-	1012	-		
Output Capacitance	Coss		-	145	-	pF	
Reverse Transfer Capacitance	Crss	I=IIVIDZ	-	121	-		
Gate resistance	Rg	f=1MHz	-	10.4	-	Ω	
Turn-On Delay Time	td _(on)	\/ O4\/ 40A	-	7	-		
Turn-On Rise Time	tr	V _{DS} =-24V, I _D =-10A,	-	3	-	ns	
Turn-Off Delay Time	td _(off)	V_{GS} =-10V, R_{G} =3 Ω	-	36	-		
Turn-Off Fall Time	tf	(11010 2)	-	40	-		
Drain-Source Diode	_						
Diode Forward Current	Is	 Tc=25°C	-	-	-31	А	
Pulsed Diode Forward Voltage	I _{SM}	10=25 C	-	-	-90		
Diode Forward Voltage	V _{SD}	I _S =-20A, V _G S=0V	-	-0.9	-1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =-20A	-	16	-	ns	
Reverse Recovery Charge	Qrr	dl _S /dt=100A/us	-	8	-	nC	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS} =-12A, V_{DD} =-30V, V_{GS} =-10V, Starting T_{J} =25°C.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

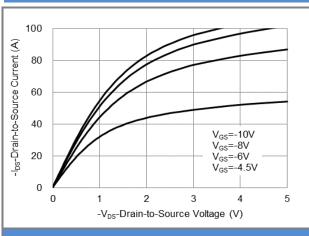


Fig.1 On-Region Characteristics

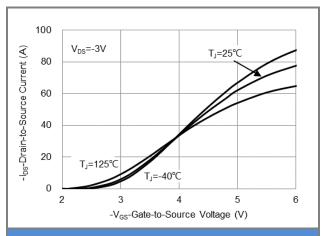


Fig.2 Transfer Characteristics

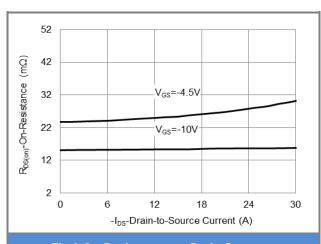


Fig.3 On-Resistance vs. Drain Current

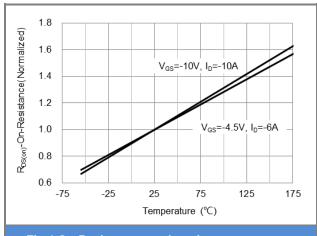


Fig.4 On-Resistance vs. Junction temperature

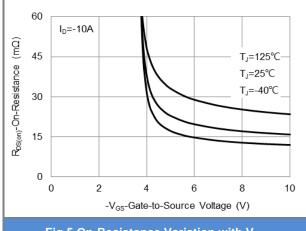
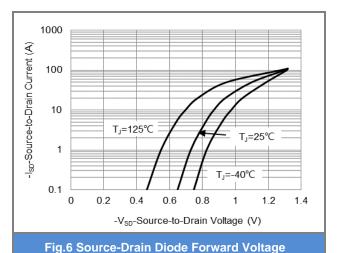


Fig.5 On-Resistance Variation with V_{GS}







TYPICAL CHARACTERISTIC CURVES

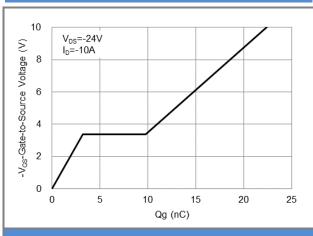


Fig.7 Gate-Charge Characteristics

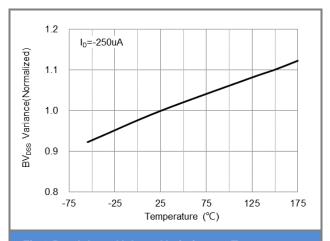


Fig.8 Breakdown Voltage Variation vs. Temperature

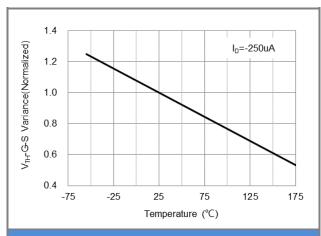


Fig.9 Threshold Voltage Variation with Temperature

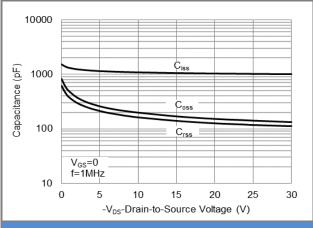
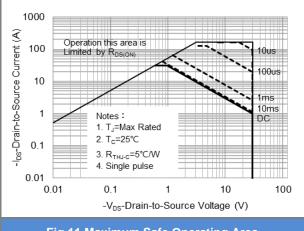


Fig.10 Capacitance vs. Drain-Source Voltage





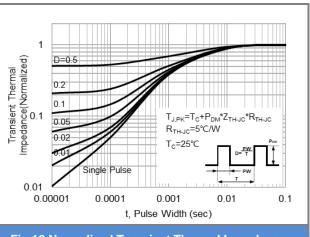


Fig.12 Normalized Transient Thermal Impedance

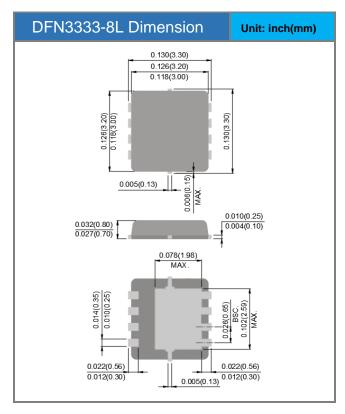


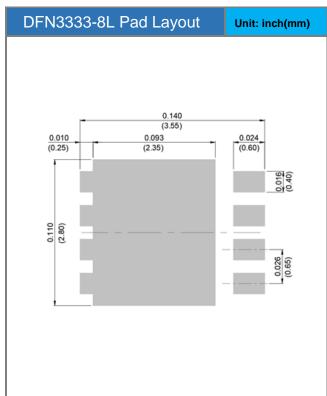


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ4439EP-AU	DFN3333-8L	5K pcs / 13" reel	439E	

Packaging Information & Mounting Pad Layout









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